

Supplemental Materials

Anisotropic magnetoresistance and electronic features of the candidate topological compound praseodymium monobismuthide

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Figure S1

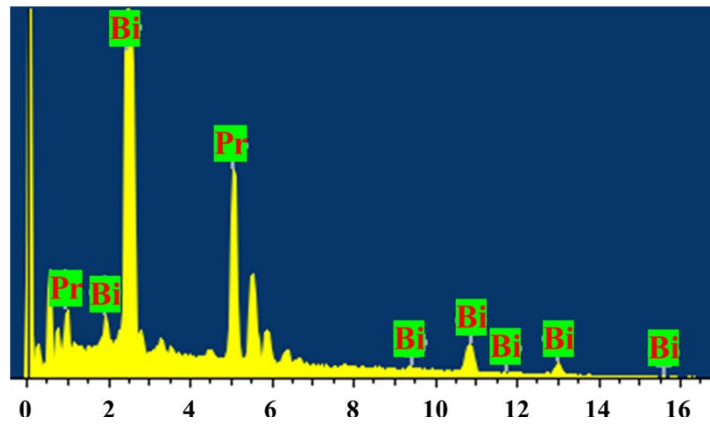


Fig. S1 EDS for our PrBi single crystal.

Figure S2

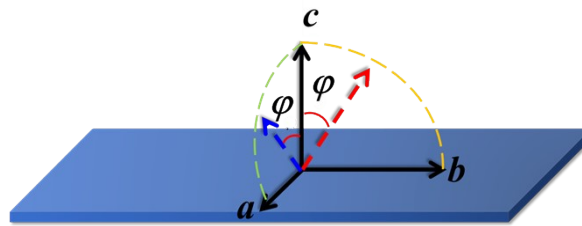


Fig. S2 Sketch of the experimental setups for angular dependent magnetoresistance measurements.

Figure S3

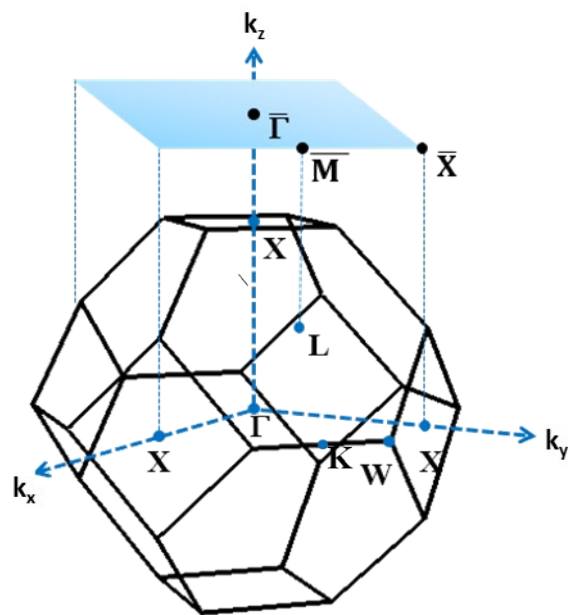


Fig. S3 Bulk Brillouin zone and the (001)-projected surface Brillouin zone.